## SENSITRON SEMICONDUCTOR

SHD126011 SHD126011P SHD126011N SHD126011D

#### TECHNICAL DATA DATASHEET 4745, REV. B.1

# SILICON SCHOTTKY RECTIFIER Ultra Low Reverse Leakage 175°C Operating Temperature

## **Applications:**

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

### Features:

- Ultra low Reverse Leakage Current
- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- For ceramic seals use part number prefix SHDC

| 5  |                     |   |             |       |
|--|---------------------|---|-------------|-------|
| Characteristics                                      | Symbol              | Condition   | Max.        | Units |
| Peak Inverse Voltage                                 | V <sub>RWM</sub>    | -   | 30          | V     |
| Max. Average Forward Current                         | I <sub>F(AV)</sub>  | Maximum DC Output Current<br>(@ T <sub>C</sub> =100 <sup>O</sup> C) (Single,<br>Doubler)              | 3.0         | A     |
| Max. Average Forward Current                         | I <sub>F(AV)</sub>  | Maximum DC Output Current<br>(@ T <sub>c</sub> =100 <sup>o</sup> C) (Common<br>Cathode, Common Anode) | 6.0         | A     |
| Max. Peak One Cycle Non-<br>Repetitive Surge Current | I <sub>FSM</sub>    | 8.3 ms, half Sine wave  | 55          | A     |
| Maximun Thermal Resistence<br>(Per leg)              | $R_{	ext{	heta}JC}$ | -   | 11.9        | °C/W  |
| Max. Junction Temperature                            | TJ                  | -   | -65 to +175 | О°    |
| Max. Storage Temperature                             | T <sub>stg</sub>    | -   | -65 to +175 | °C    |

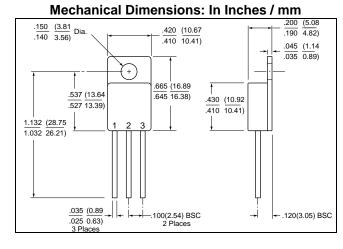
## **Maximum Ratings:**

## **Electrical Characteristics:**

| Characteristics           | Symbol          | Condition                                    | Max. | Units |
|---------------------------|-----------------|--|------|-------|
| Max. Forward Voltage Drop | V <sub>F1</sub> | @ 3A, Pulse, T <sub>J</sub> = 25 °C          | 0.59 | V     |
|                           | V <sub>F2</sub> | @ 3A, Pulse, T <sub>J</sub> = 125 °C         | 0.49 | V     |
| Max. Reverse Current      | I <sub>R1</sub> | $@V_R = 30V$ , Pulse,                        | 0.4  | mA    |
|                           |                 | $T_J = 25 \ ^{\circ}C$                       |      |       |
|                           | I <sub>R2</sub> | $@V_R = 30V$ , Pulse,                        | 20   | mA    |
|                           |                 | T <sub>J</sub> = 125 °C                      |      |       |
| Max. Junction Capacitance | CT              | @V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C | 220  | pF    |
|                           |                 | f <sub>SIG</sub> = 1MHz,                     |      |       |
|                           |                 | $V_{SIG} = 50 \text{mV} (\text{p-p})$        |      |       |

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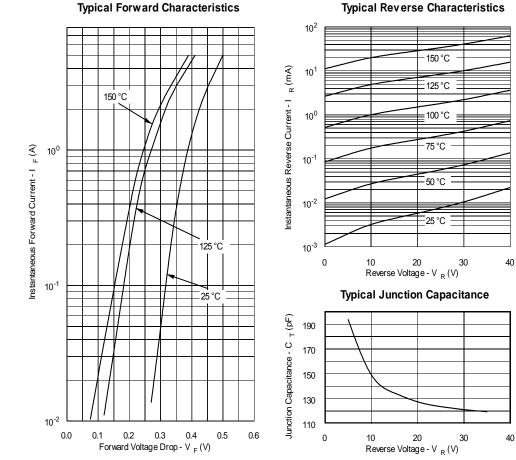
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## <u>TO-257</u>

| DEVICE TYPE        | PIN 1     | PIN 2           | PIN 3     |
|--------------------|-----------|-----------------|-----------|
| SINGLE RECTIFIER   | CATHODE   | ANODE           | ANODE     |
| COMMON CATHODE (P) | ANODE 1   | COMMON CATHODE  | ANODE 2   |
| COMMON ANODE (N)   | CATHODE 1 | COMMON ANODE    | CATHODE 2 |
| DOUBLER (D)        | ANODE     | CATHODE / ANODE | CATHODE   |

Note: Vf characteristics are for unpackaged die only.



**Typical Reverse Characteristics** 

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